HALOGEN



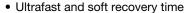
Vishay Semiconductors

Ultrafast Rectifier, 8 A FRED Pt®



PRIMARY CHARACTERISTICS								
I _{F(AV)}	8 A							
V_{R}	1200 V							
V _F at I _F at 125 °C	1.95 V							
t _{rr} typ.	42 ns							
T _J max.	175 °C							
Package	TO-220AC 2L							
Circuit configuration	Single							

FEATURES



• Optimized forward voltage drop

Polyimide passivation

• 175 °C maximum operating junction temperature

Rugged design

- Good thermal performance
- Meets JESD 201 class 1A whisker test
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

DESCRIPTION / APPLICATIONS

Ultrafast recovery rectifiers designed with optimized forward voltage drop, ultrafast recovery time, and soft recovery. Polyimide passivated with a planar structure and platinum doped life time control guarantee ruggedness, reliability, and offer a solid value for efficiency and thermal performance.

These devices are intended for use in boost stage in the AC/DC section of SMPS, high frequency output rectification of battery chargers, inverters for solar inverters or as freewheeling diodes in motor drives.

ABSOLUTE MAXIMUM RATINGS										
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS						
Repetitive peak reverse voltage	V_{RRM}		1200	V						
Average rectified forward current	I _{F(AV)}	$T_C = 140 ^{\circ}C, D = 0.50$	8							
Non-repetitive peak surge current	I _{FSM}	T_C = 25 °C, t_p = 10 ms, sine wave	80	А						
Repetitive peak forward current	I _{FRM}		16							
Operating junction and storage temperatures	T _J , T _{Stg}		-55 to +175	°C						

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)										
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS				
Breakdown voltage, blocking voltage	V_{BR} , V_{R}	I _R = 200 μA	1200	-	-					
Forward voltage	V _F	I _F = 8 A	ı	2.05	2.55	V				
Forward voltage		I _F = 8 A, T _J = 125 °C	-	1.95	2.37					
Deverage leake as a surrent	I _R	$V_R = V_R$ rated	-	-	55					
Reverse leakage current		T _J = 125 °C, V _R = V _R rated	-	-	100	μA				
Junction capacitance	C _T	V _R = 200 V	-	8	=	pF				
Series inductance	L _S	Measured lead to lead 5 mm from package body	-	8.0	-	nH				



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DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)										
PARAMETER	SYMBOL	TEST CONDITION	S	MIN.	TYP.	MAX.	UNITS			
Reverse recovery time		$I_F = 1.0 \text{ A}, dI_F/dt = 1.0 \text{ A}$	-	42	-					
	t _{rr}	T _J = 25 °C		-	144	-	ns			
		T _J = 125 °C		-	204	-				
Dools woods on a surrent		T _J = 25 °C	I _F = 8 A	-	5	-	Α			
Peak recovery current	IRRM	T _J = 125 °C	$dI_F/dt = 100 A/\mu s$ $V_R = 390 V$	-	7.2	-				
Reverse recovery charge	0	T _J = 25 °C] ''	-	370	-	nC			
	Q_{rr}	T _J = 125 °C		-	745	-				

THERMAL - MECHANICAL SPECIFICATIONS										
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS				
Thermal resistance, junction to case	R_{thJC}		-	1.25	1.5					
Thermal resistance, junction to case	R_{thJA}	Typical socket mount	-	54	60	°C/W				
Thermal resistance, case to heat sink	R _{thCS}	Mounting surface, flat, smooth, and greased	-	0.18	0.4					
Weight			-	0.2	-	g				
weight			-	0.07	-	oz.				
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)				
Marking device		Case style TO-220AC 2L	8ETU12							

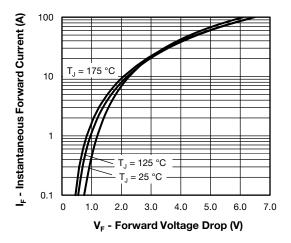


Fig. 1 - Typical Forward Voltage Drop Characteristics

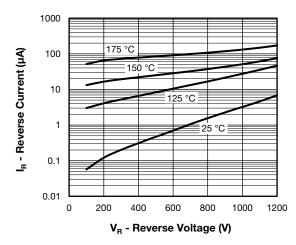


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage



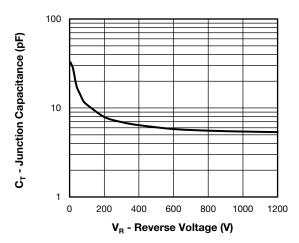


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

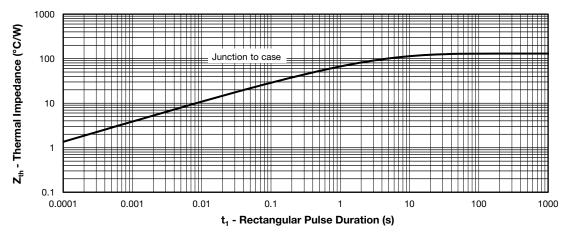


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

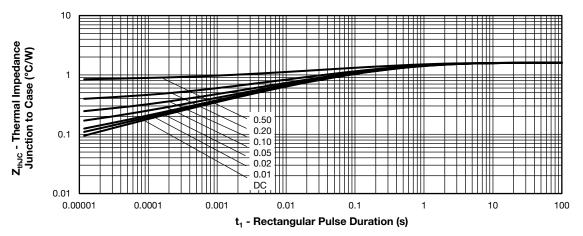


Fig. 5 - Maximum Thermal Impedance ZthJC Characteristics



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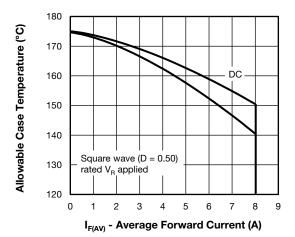


Fig. 6 - Maximum Allowable Case Temperature vs. Average Forward Current

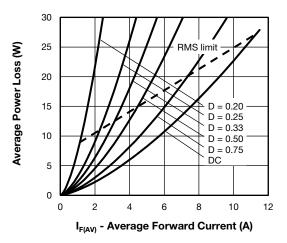


Fig. 7 - Forward Power Loss Characteristics

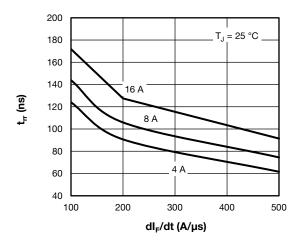


Fig. 8 - Typical Reverse Recovery Time vs. dI_F/dt

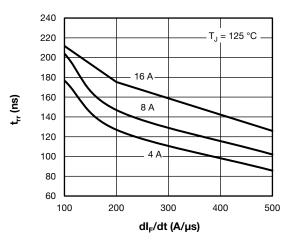


Fig. 9 - Typical Reverse Recovery Time vs. dl_F/dt

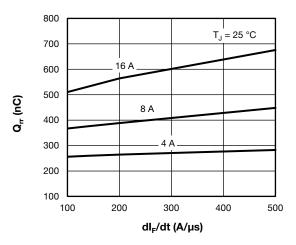


Fig. 10 - Typical Stored Charge vs. dl_F/dt

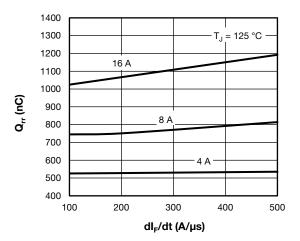


Fig. 11 - Typical Stored Charge vs. dI_F/dt



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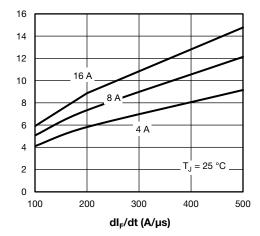


Fig. 12 - Typical Reverse Current vs. dl_F/dt

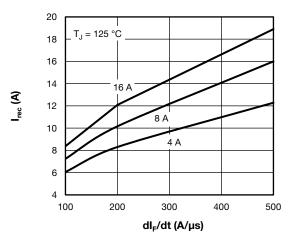
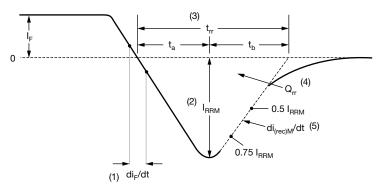


Fig. 13 - Typical Reverse Current vs. dl_F/dt



- (1) di_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) $\rm t_{rr}$ reverse recovery time measured from zero crossing point of negative going $\rm l_{r}$ to point where a line passing through 0.75 $\rm l_{RRM}$ and 0.50 $\rm l_{RRM}$ extrapolated to zero current.
- (4) \mathbf{Q}_{rr} area under curve defined by \mathbf{t}_{rr} and \mathbf{I}_{RRM}

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) di_{(rec)M}/dt - peak rate of change of current during t_b portion of t_{rr}

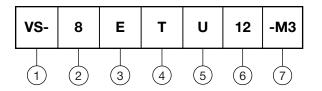
Fig. 14 - Reverse Recovery Waveform and Definitions



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ORDERING INFORMATION TABLE

Device code



1 - Vishay Semiconductors product

Current rating (8 = 8 A)

3 - E = single

4 - Package:

T = 2L TO-220AC

5 - U = ultrafast recovery

6 - Voltage rating (12 = 1200 V)

7 - Environmental digit:

-M3 = halogen-free, RoHS-compliant, and termination lead (Pb)-free

ORDERING INFORMATION (Example)									
PREFERRED P/N	FERRED P/N BASE QUANTITY PACKAGING DESCRIPTION								
VS-8ETU12-M3	50	Antistatic plastic tubes							

LINKS TO RELATED DOCUMENTS							
Dimensions <u>www.vishay.com/doc?96156</u>							
Part marking information	www.vishay.com/doc?95391						



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TO-220AC 2L

DIMENSIONS in millimeters and inches





Conforms to JEDEC® outline TO-220AC

SYMBOL	MILLIM	MILLIMETERS		HES	NOTES	NOTES	SYMBOL	MILLIN	IETERS	INC	HES	NOTES
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES	NOTES	STIVIBOL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.25	4.65	0.167	0.183			D2	11.68	13.30	0.460	0.524	6, 7
A1	1.14	1.40	0.045	0.055			Е	10.11	10.51	0.398	0.414	3, 6
A2	2.50	2.92	0.098	0.115			E1	6.86	8.89	0.270	0.350	6
b	0.69	1.01	0.027	0.040			е	2.41	2.67	0.095	0.105	
b1	0.38	0.97	0.015	0.038	4		e1	4.88	5.28	0.192	0.208	
b2	1.20	1.73	0.047	0.068			H1	6.09	6.48	0.240	0.255	6
b3	1.14	1.73	0.045	0.068	4		L	13.52	14.02	0.532	0.552	
С	0.36	0.61	0.014	0.024			L1	3.32	3.82	0.131	0.150	2
c1	0.36	0.56	0.014	0.022	4		ØΡ	3.54	3.91	0.139	0.154	
D	14.85	15.35	0.585	0.604	3		Q	2.60	3.00	0.102	0.118	
D1	8.38	9.02	0.330	0.355				•	•			

Notes

- ⁽¹⁾ Dimensioning and tolerancing as per ASME Y14.5M-1994
- (2) Lead dimension and finish uncontrolled in L1
- (3) Dimension D, D1, and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Dimension b1, b3, and c1 apply to base metal only
- Controlling dimensions: inches
- (6) Thermal pad contour optional within dimensions E, H1, D2, and E1
- (7) Outline conforms to JEDEC® TO-220, except D2



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